

FIG. 1

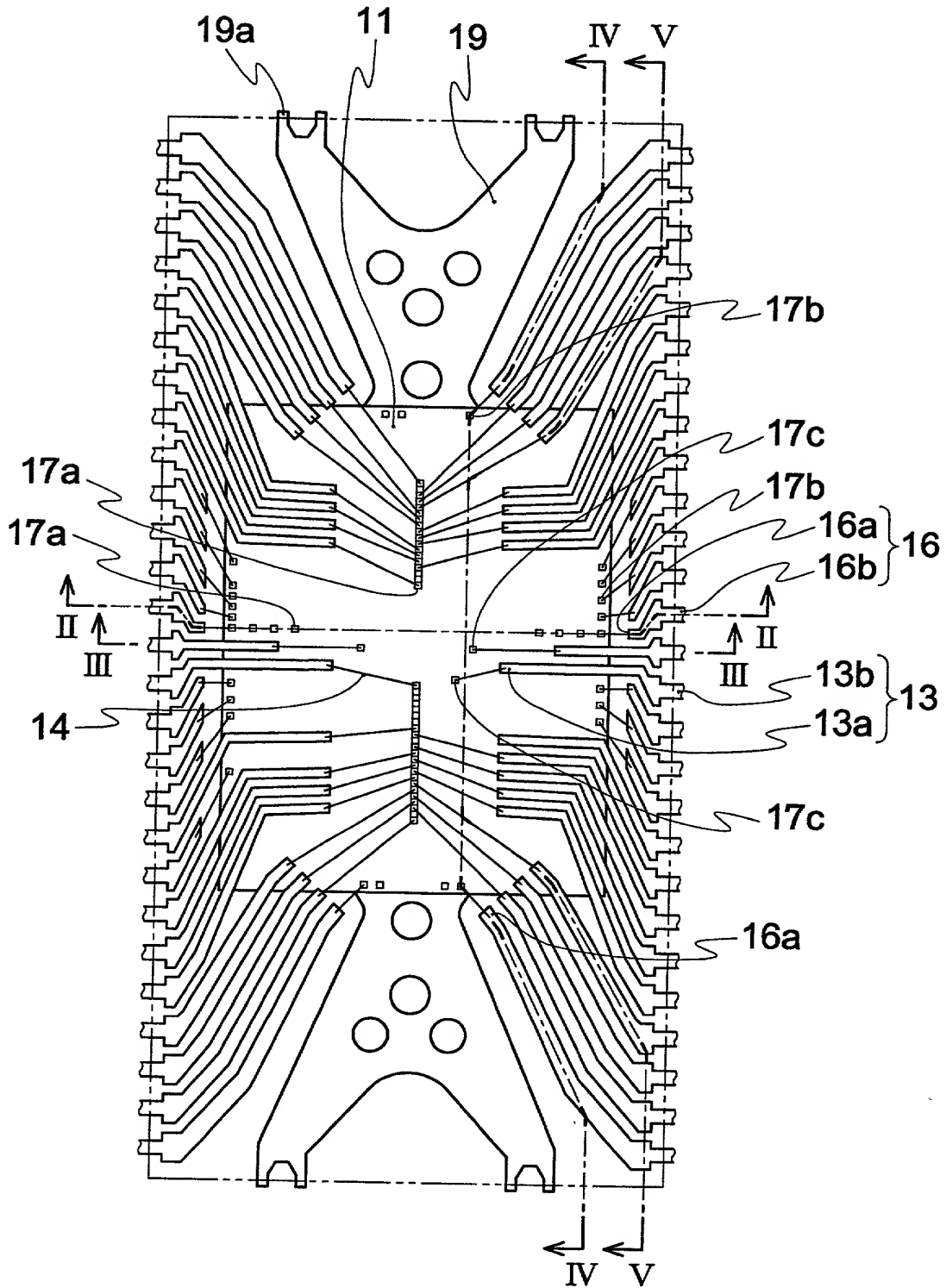


FIG. 2

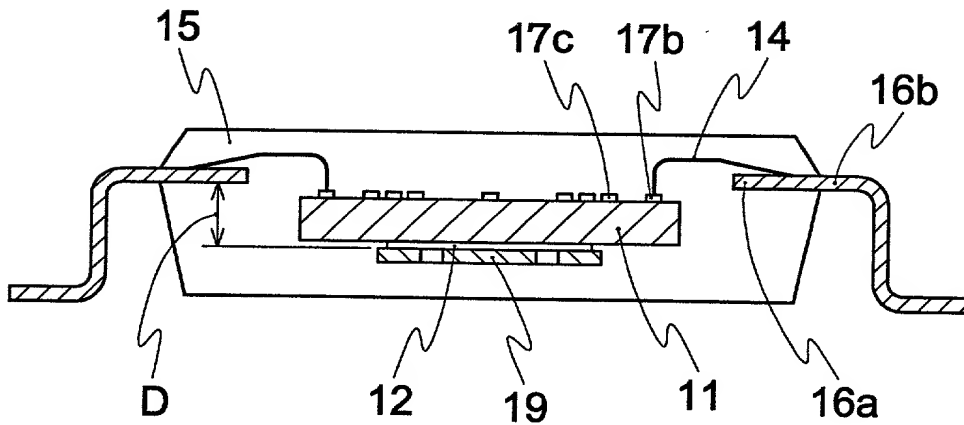


FIG. 3

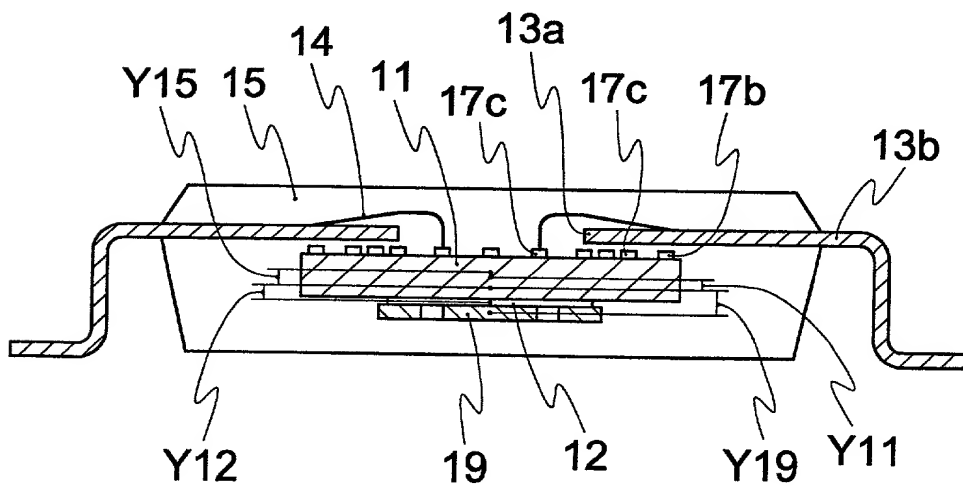


Fig. 1 is a cross-sectional view of a semiconductor device. The device consists of a substrate 11, a thin layer 12, a series of rectangular blocks 17a, 17b, and 17c, a layer 19, a layer 16a, and a layer 19a. The blocks 17a, 17b, and 17c are arranged in a row on the thin layer 12. The layer 19 covers the blocks and the substrate. The layer 16a is on top of the layer 19, and the layer 19a is on top of the layer 16a. A dimension D is indicated between the substrate 11 and the layer 19a.

FIG. 6

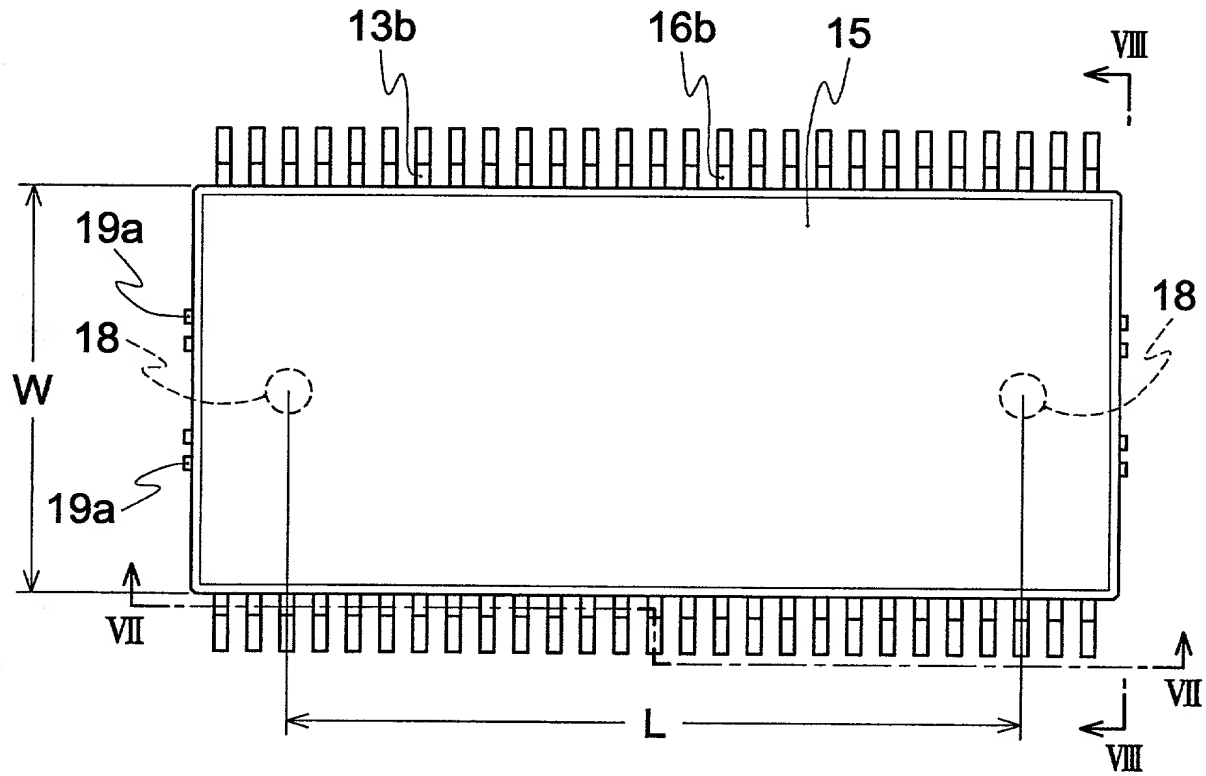


FIG. 7

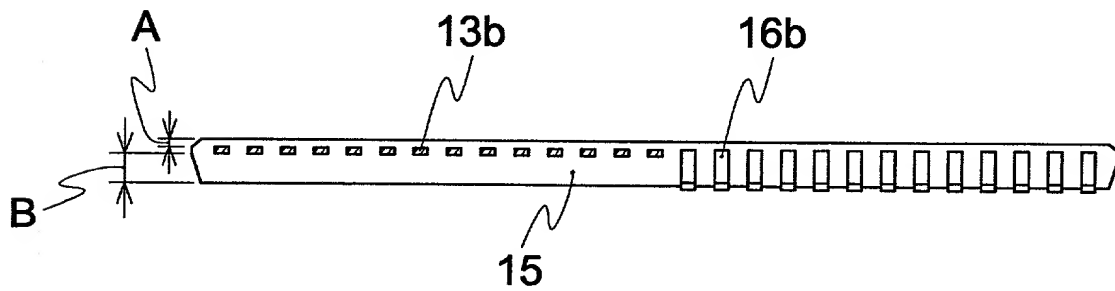


FIG. 8

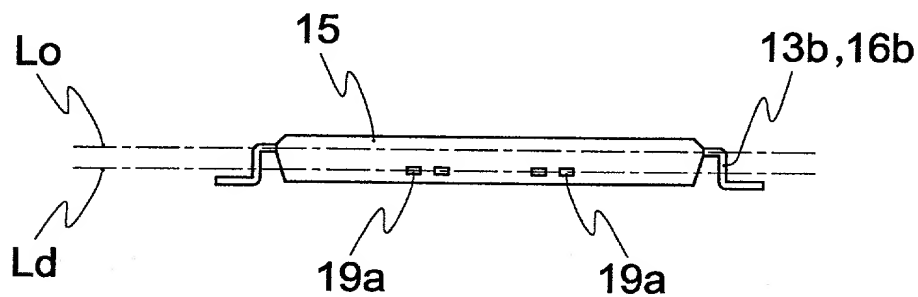


FIG. 9

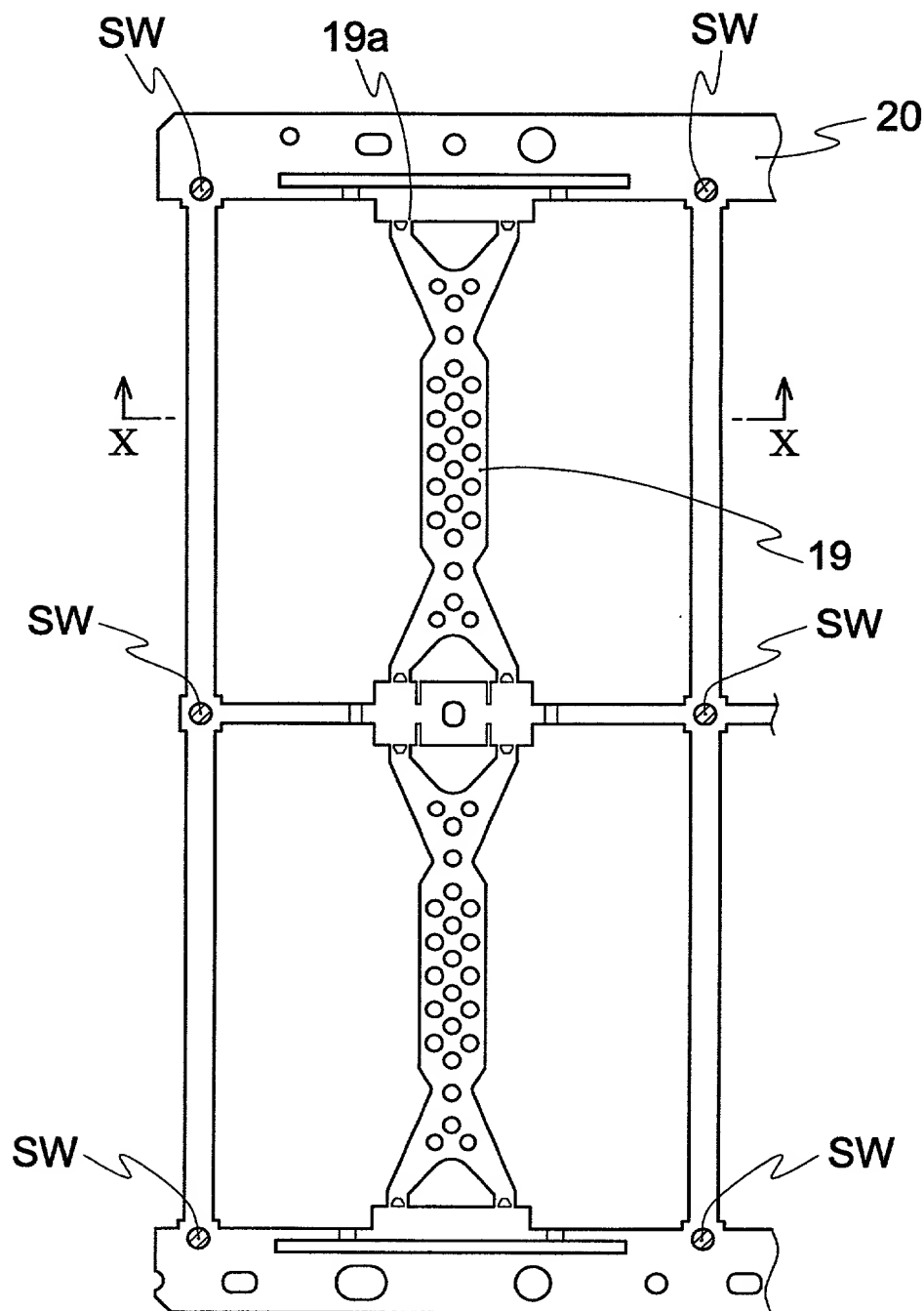


FIG. 10

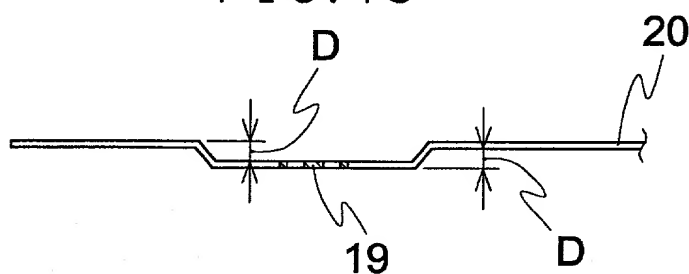


FIG. 11

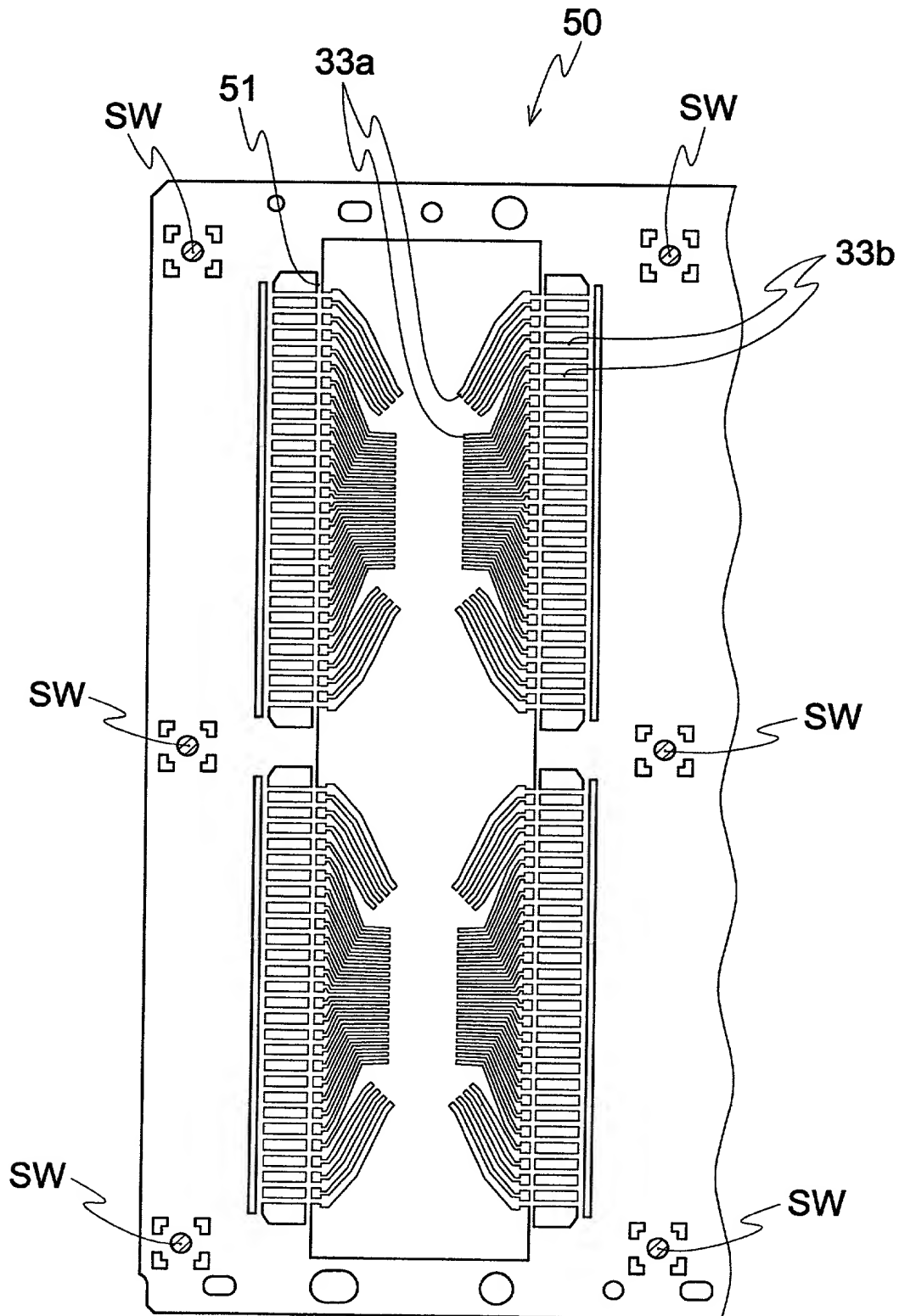




FIG. 13

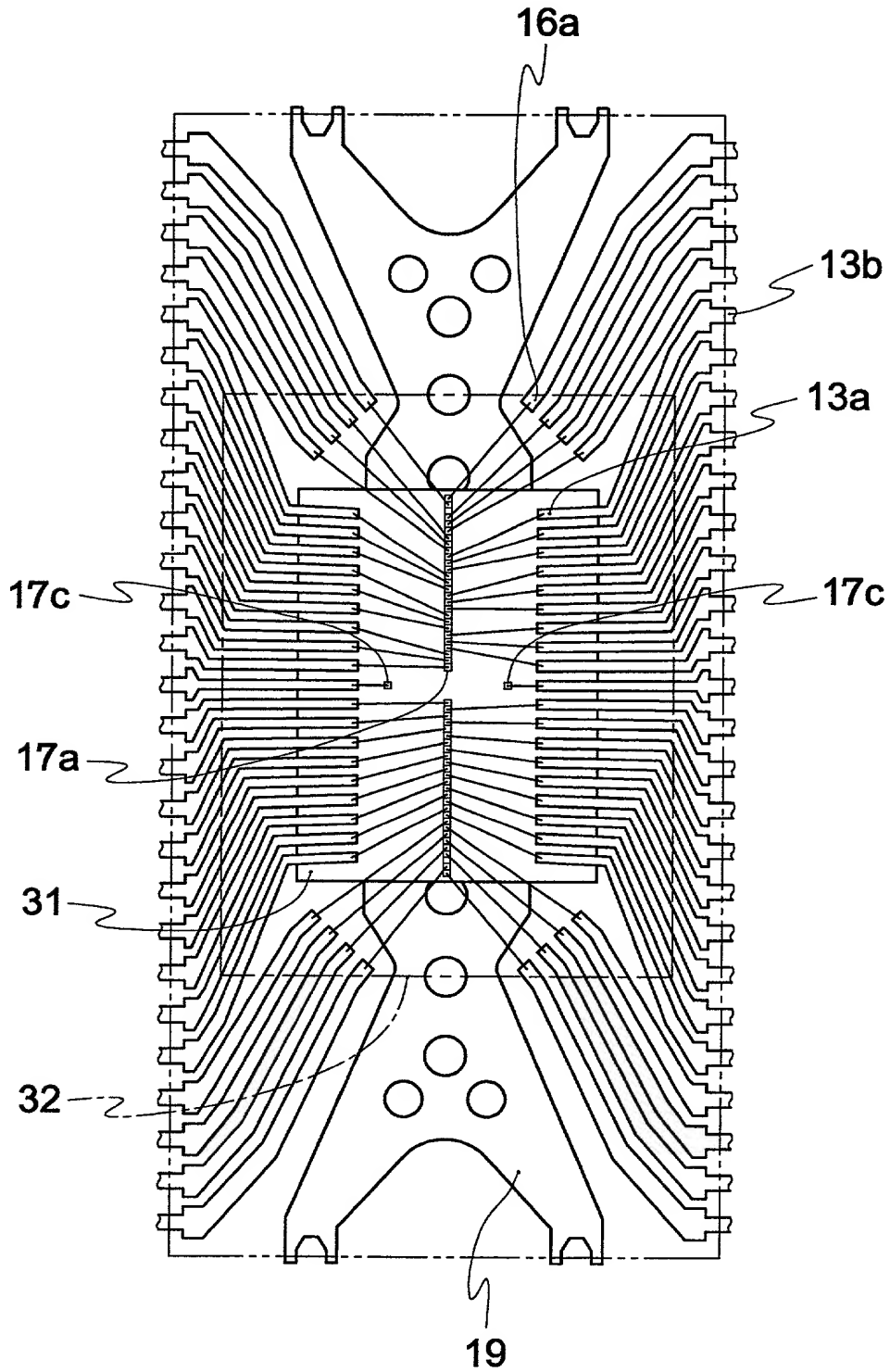




FIG. 14

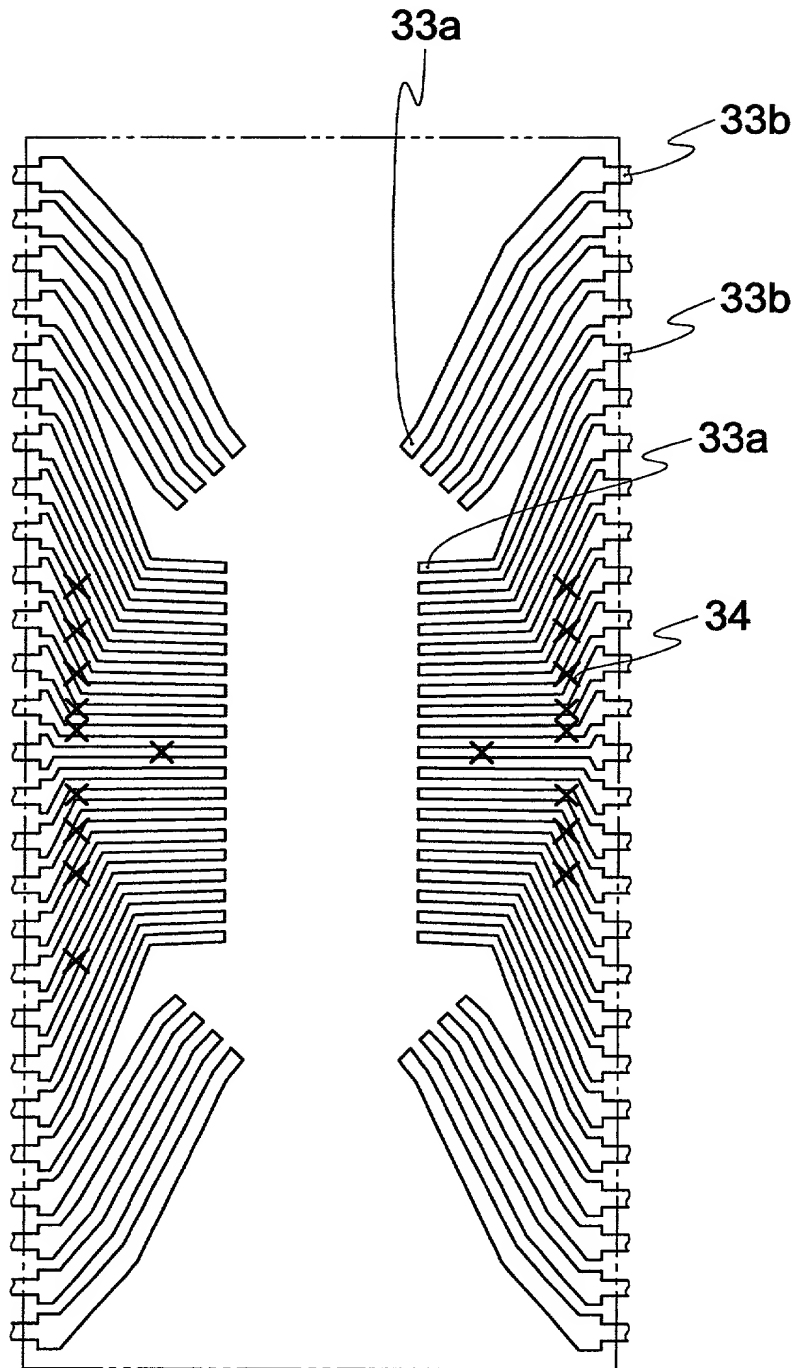


FIG. 15

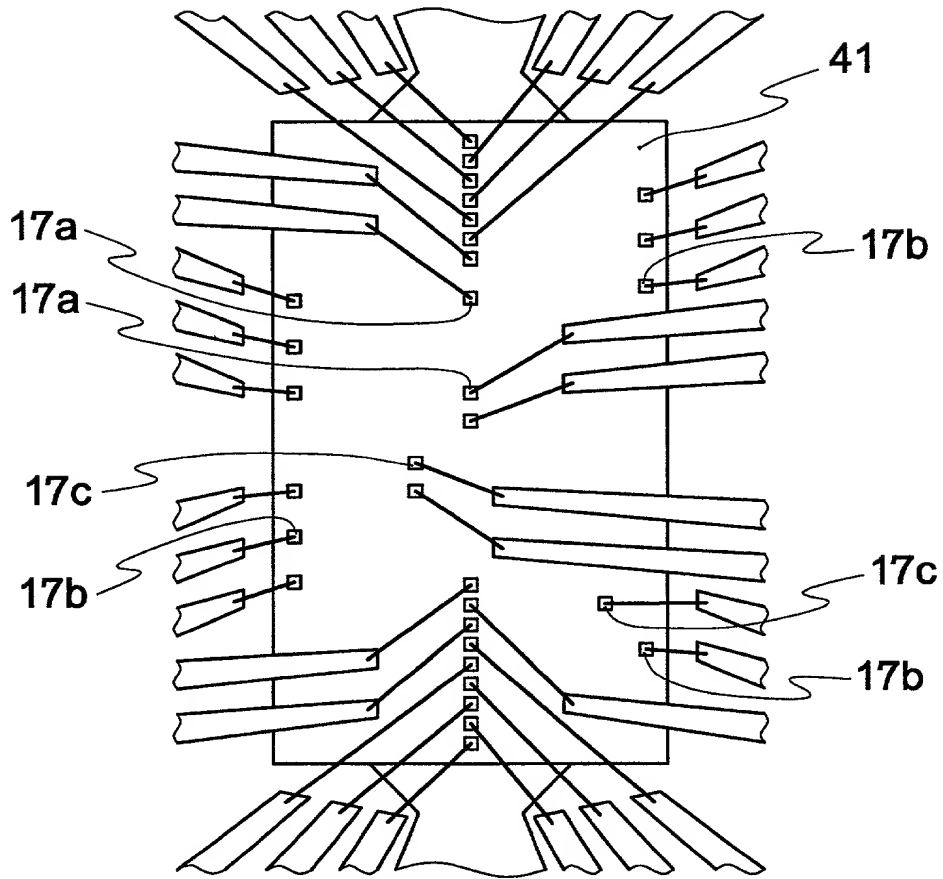


FIG. 16

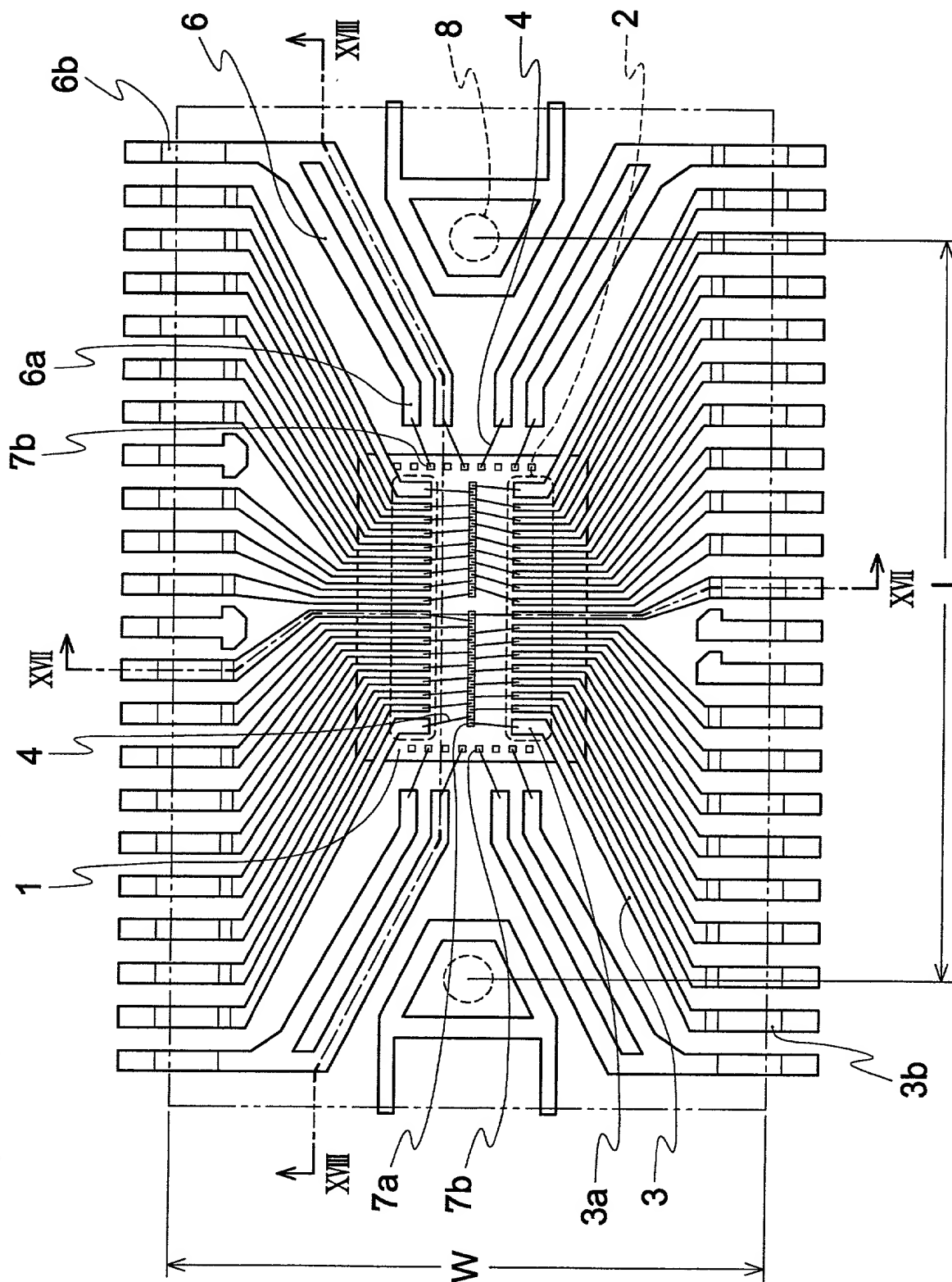


FIG. 17

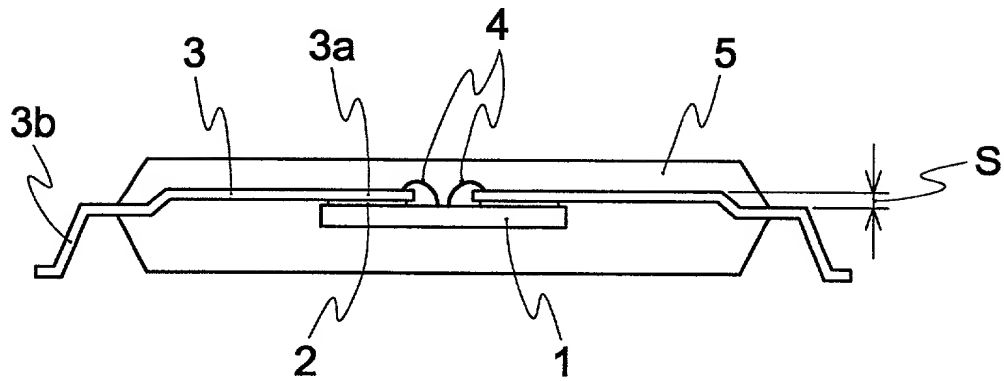


FIG. 18

